

**Features**

- SiC MOSFET Technology
- High Speed Switching
- Reduction Of Heat Sink Requirements
- Essentially No Switching Losses
- Halogen Free. "Green" Device (Note 1)
- Lead Free Finish/RoHS Compliant("P" Suffix Designates RoHS Compliant. See Ordering Information) (Note2)

**Maximum Ratings**

- Operating Junction Temperature Range : -55°C to +175°C
- Storage Temperature Range: -55°C to +175°C
- Thermal Resistance Junction to Ambient,Max(Note 3): 62°C/W
- Thermal Resistance Junction to Case,Typ : 0.46°C/W

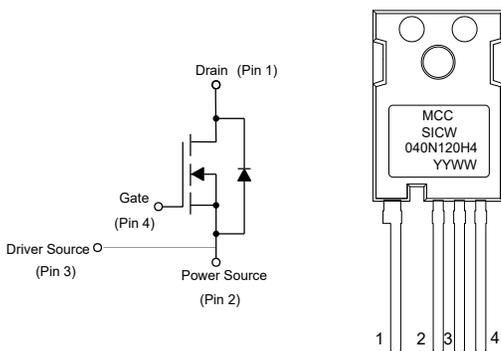
**Applications**

- Solar Inverters
- Uninterruptible Power Supply
- Photovoltaic Inverter
- Battery Chargers
- Motor Drives

Parameter	Symbol	Rating	Unit	
Drain-Source Voltage	$V_{DS}$	1200	V	
Gate-Source Voltage(Note 4)	$V_{GSmax}$	-10/+25	V	
Gate-Source Voltage	$V_{GSop}$	-5/+20	V	
Continuous Drain Current $V_{GS}=20V$	$I_D$	$T_C=25^{\circ}C$	62	A
		$T_C=110^{\circ}C$	42	
Pulsed Drain Current (Note 5)	$I_{DM}$	223	A	
Total Power Dissipation	$P_D$	$T_C=25^{\circ}C$	326	W
		$T_C=110^{\circ}C$	141	
Avalanche Energy, Single Pulse	$V_{DD}=100V, I_D=12A$	$E_{AS}$	1.875	J

Note1:Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.  
 Note2:High Temperature Solder Exemptions Applied, see EU Directive Annex 7a.  
 Note3:Device in a still air environment with  $T_A=25^{\circ}C$ .  
 Note4:AC f > 1Hz, duty cycle < 1%  
 Note5:Pulse Test: Pulse Width Limited by  $T_{jmax}$ .

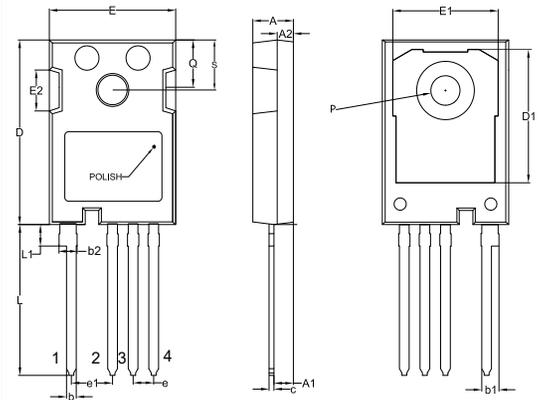
**Internal Structure and Marking Code**



Device Code: SICW040N120H4  
 Date Code: YYWW (Year & Week)

**SiC  
N-CHANNEL  
MOSFET**

**TO-247-4**



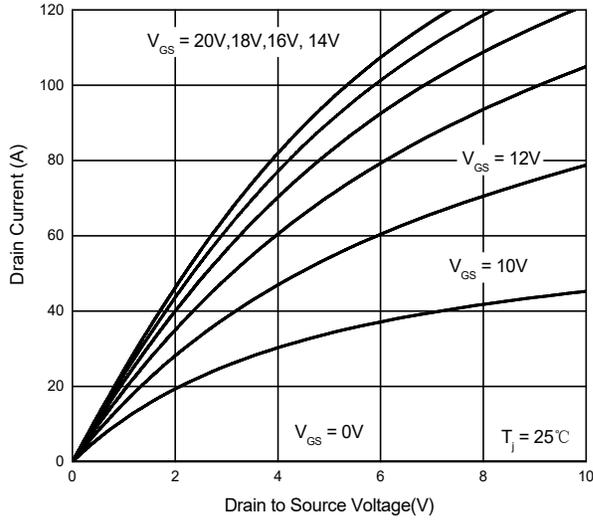
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.189	0.205	4.80	5.20	
A1	0.090	0.098	2.29	2.50	
A2	0.074	0.082	1.88	2.08	
b	0.043	0.054	1.10	1.36	
b1	0.093	0.108	2.35	2.75	
b2	0.094	0.112	2.39	2.84	
c	0.022	0.028	0.55	0.70	
D	0.917	0.929	23.30	23.60	
D1	0.640	0.663	16.25	16.85	
E	0.620	0.632	15.75	16.05	
E1	0.543	0.559	13.80	14.20	
E2	0.173	0.201	4.4	5.10	
e	0.100		2.54		
e1	0.199		5.06		
L	0.683	0.694	17.34	17.64	
L1	0.157	0.169	4.00	4.30	
P	0.138	0.148	3.51	3.75	Φ
Q	0.220	0.236	5.60	6.00	
S	0.220	0.248	5.60	6.30	

**Electrical Characteristics @ T<sub>j</sub>=25°C (Unless Otherwise Specified)**

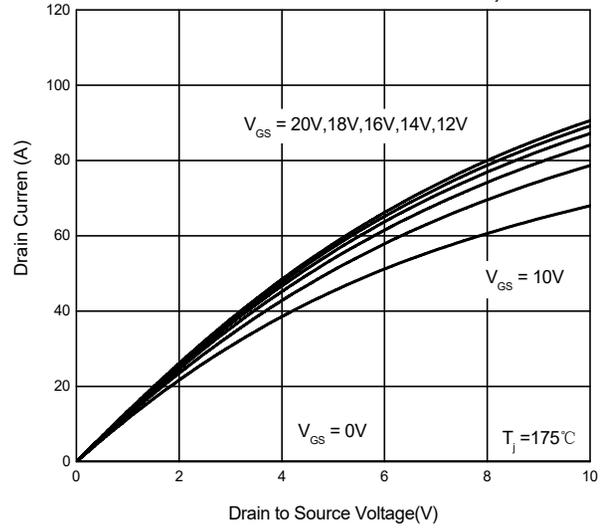
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit	
<b>Static Characteristics</b>							
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =100μA	1200			V	
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =20V			250	nA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =1200V, V <sub>GS</sub> =0V			50	μA	
Gate-Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =40mA	2	2.7	4.5	V	
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =20V, I <sub>D</sub> =30A		40	52	mΩ	
		V <sub>GS</sub> =20V, I <sub>D</sub> =30A, T <sub>j</sub> =175°C		75		mΩ	
Internal Gate Resistance	R <sub>g</sub>	f=1MHz, V <sub>AC</sub> =25mV		0.9		Ω	
Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =15V, I <sub>D</sub> =30A		15		S	
<b>Dynamic Characteristics</b>							
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =800V, V <sub>GS</sub> =0V, f=1MHz, V <sub>AC</sub> =25mV		3619		pF	
Output Capacitance	C <sub>oss</sub>			145			
Reverse Transfer Capacitance	C <sub>rss</sub>			18			
Coss Stored Energy	E <sub>oss</sub>			59		μJ	
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =800V, V <sub>GS</sub> =-5/+20V, I <sub>D</sub> =30A		229		nC	
Gate-Source Charge	Q <sub>gs</sub>			68			
Gate-Drain Charge	Q <sub>gd</sub>			66			
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =800V, V <sub>GS</sub> =-4/+20V, R <sub>G</sub> =2.7Ω, I <sub>D</sub> =30A, R <sub>L</sub> =27Ω		26		ns	
Rise Time	t <sub>r</sub>			50			
Turn-Off Delay Time	t <sub>d(off)</sub>			7			
Fall Time	t <sub>f</sub>			11			
Turn-On switching energy	E <sub>on</sub>	V <sub>DD</sub> =800V, V <sub>GS</sub> =0/+20V, R <sub>G</sub> =2.7Ω, I <sub>D</sub> =30A		83		μJ	
Turn-Off switching energy	E <sub>off</sub>			128			
<b>Diode Characteristics</b>							
Continuous Body Diode Current	I <sub>S</sub>	V <sub>GS</sub> =0V, T <sub>C</sub> =25°C		48		A	
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>SD</sub> =7.5A		2.9		V	
Reverse Recovery Time	t <sub>rr</sub>	V <sub>GS</sub> =0V, I <sub>SD</sub> =30A, V <sub>DS</sub> =400V, dI <sub>F</sub> /dt=300A/μs		59		ns	
Reverse Recovery Charge	Q <sub>rr</sub>				212		nC
Peak Reverse Recovery Current	I <sub>rrm</sub>				5.1		A

**Curve Characteristics** ( $T_J=25^\circ\text{C}$  unless otherwise specified)

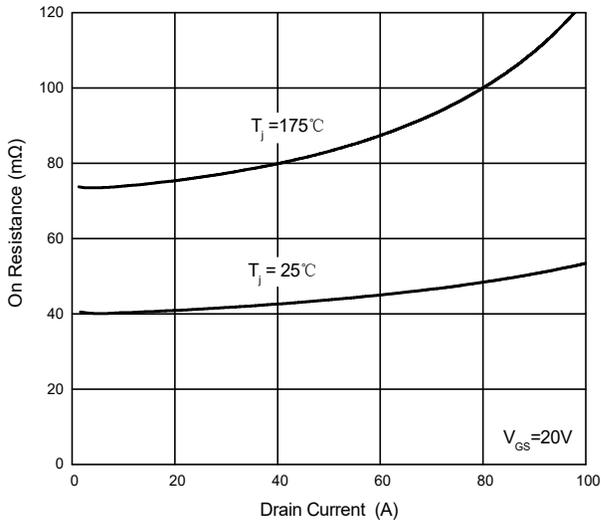
**Fig. 1 - Typical Output Characteristic ( $T_J=25^\circ\text{C}$ )**



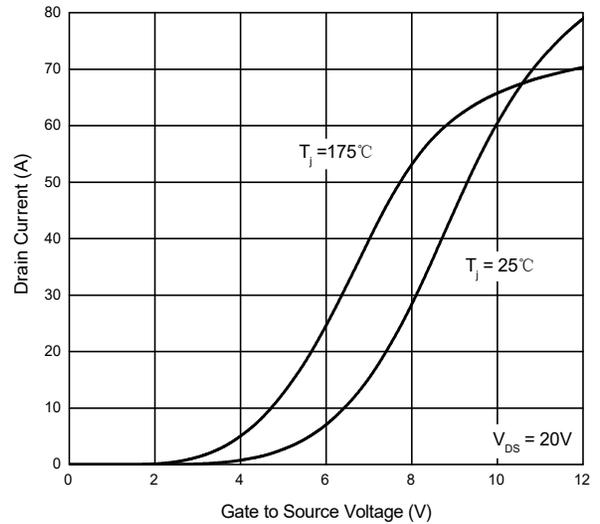
**Fig. 2 - Typical Output Characteristic ( $T_J=175^\circ\text{C}$ )**



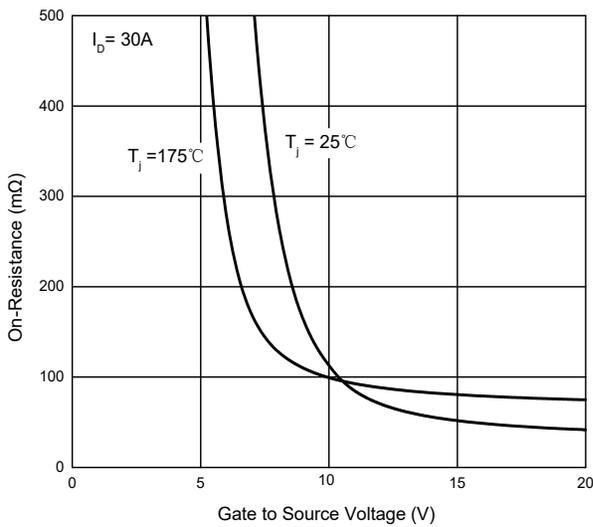
**Fig. 3 - On-Resistance vs. Drain Current**



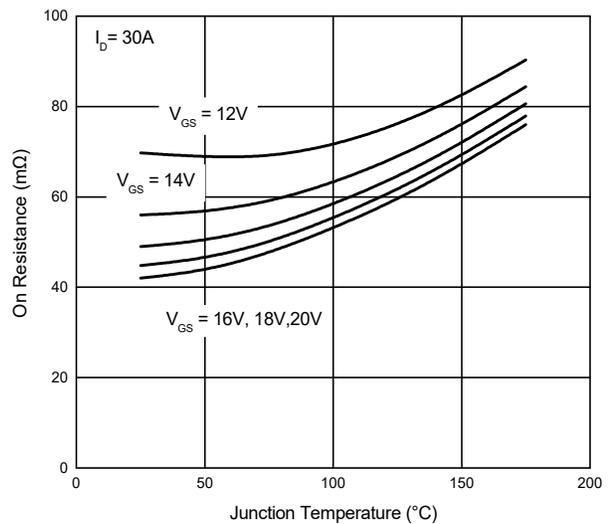
**Fig. 4 - Typical Transfer Characteristic**



**Fig. 5 - On-Resistance vs. Gate Voltage**

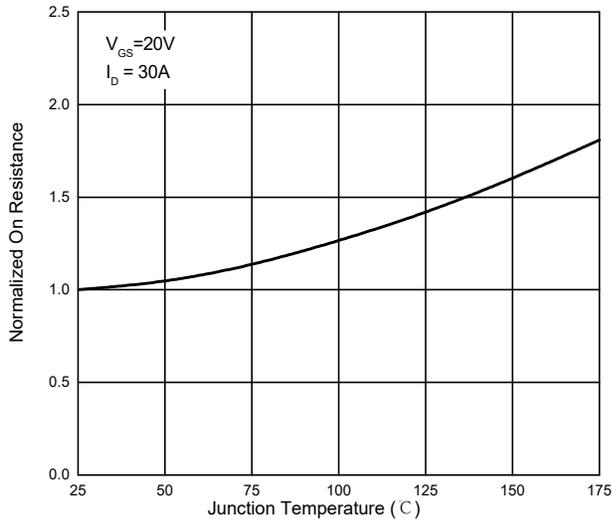


**Fig. 6 - On-Resistance vs. Temperature**

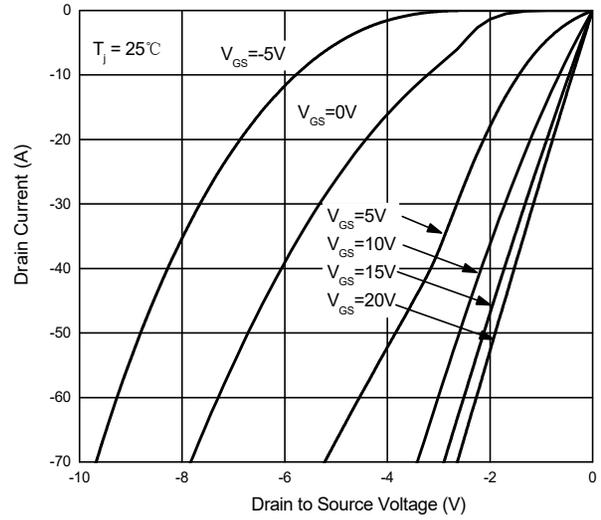


**Curve Characteristics** ( $T_J=25^\circ\text{C}$  unless otherwise specified)

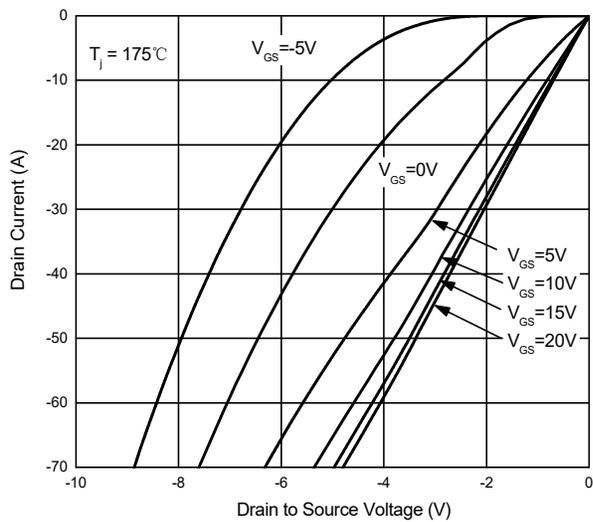
**Fig. 7 - Normalized On-Resistance vs. Temperature**



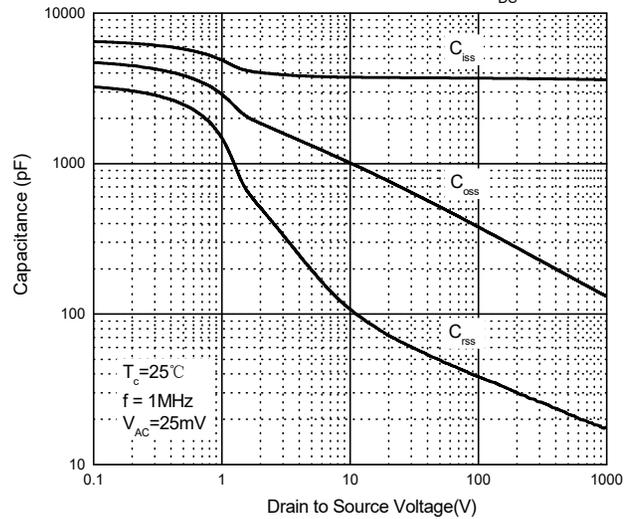
**Fig. 8 - Reverse Output Voltage**



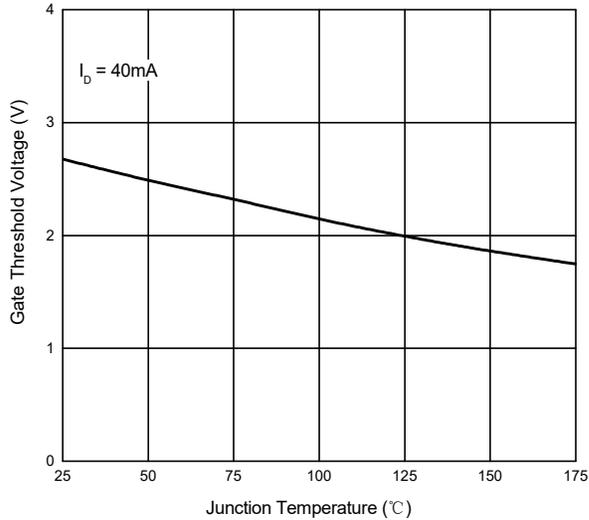
**Fig. 9 - Reverse Output Voltage**



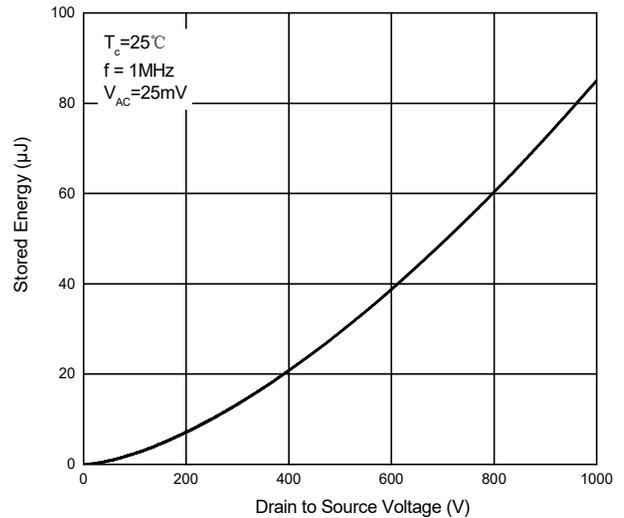
**Fig. 10 - Capacitances vs.  $V_{DS}$**



**Fig. 11 - Threshold Voltage vs. Temperature**

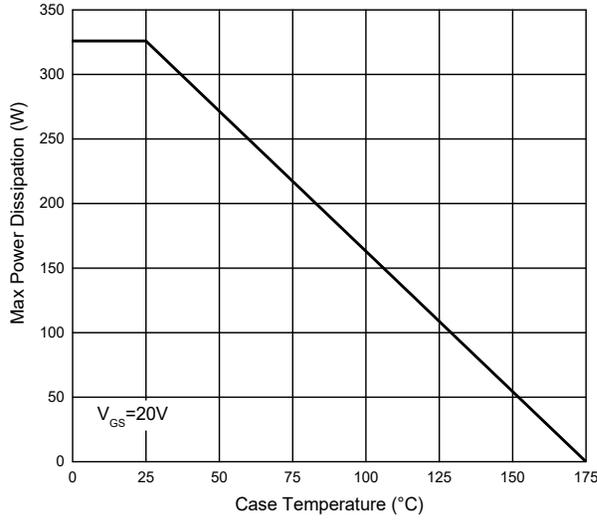


**Fig. 12 - Output Capacitor Stored Energy**

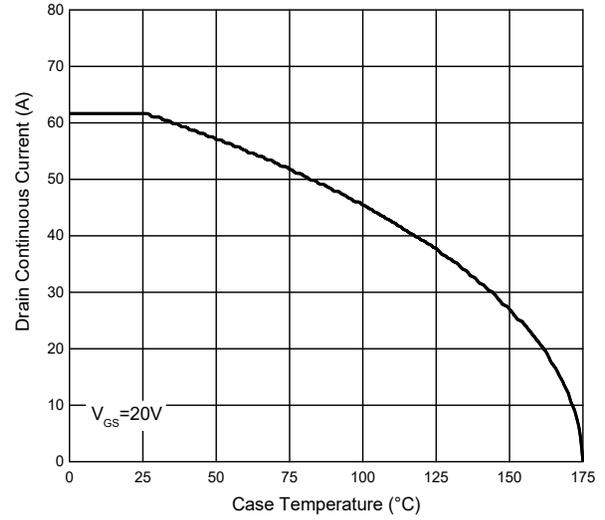


**Curve Characteristics** ( $T_J=25^\circ\text{C}$  unless otherwise specified)

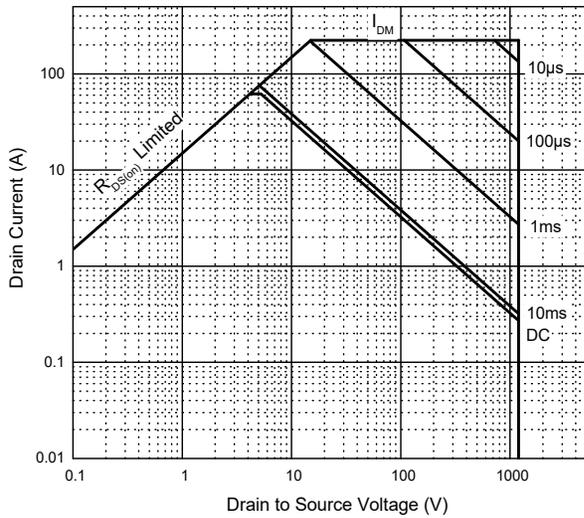
**Fig. 13 - Power Derating**



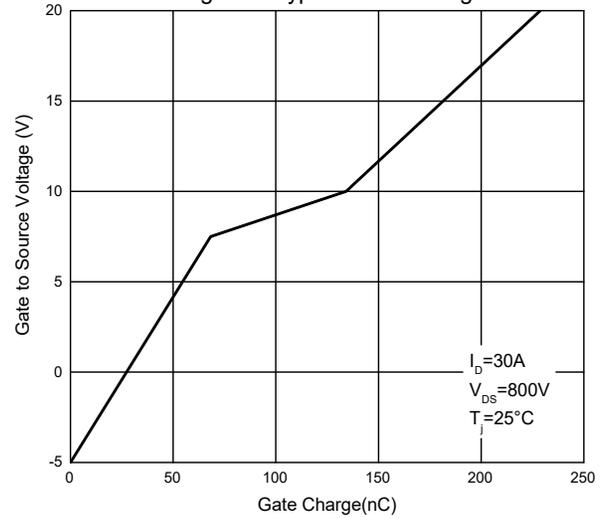
**Fig. 14 - Drain Current Derating**



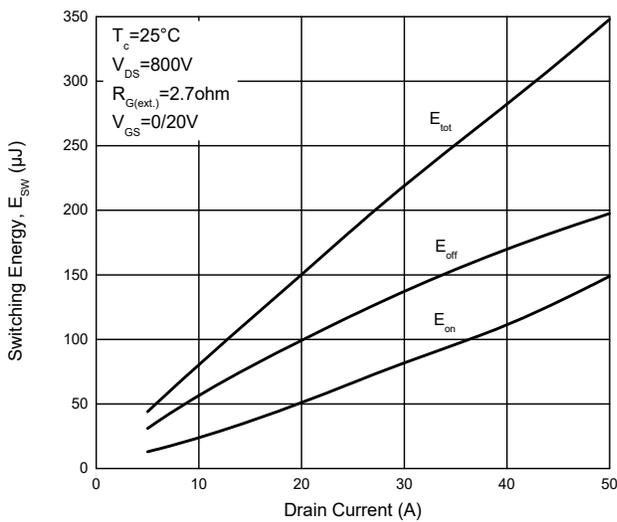
**Fig. 15 - Safe Operation Area**



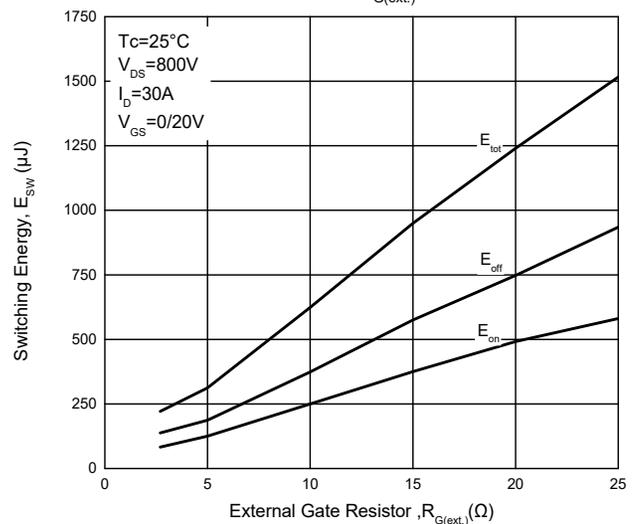
**Fig. 16 - Typical Gate Charge**



**Fig. 17 - Clamped Inductive Switching Energy vs. Drain Current**

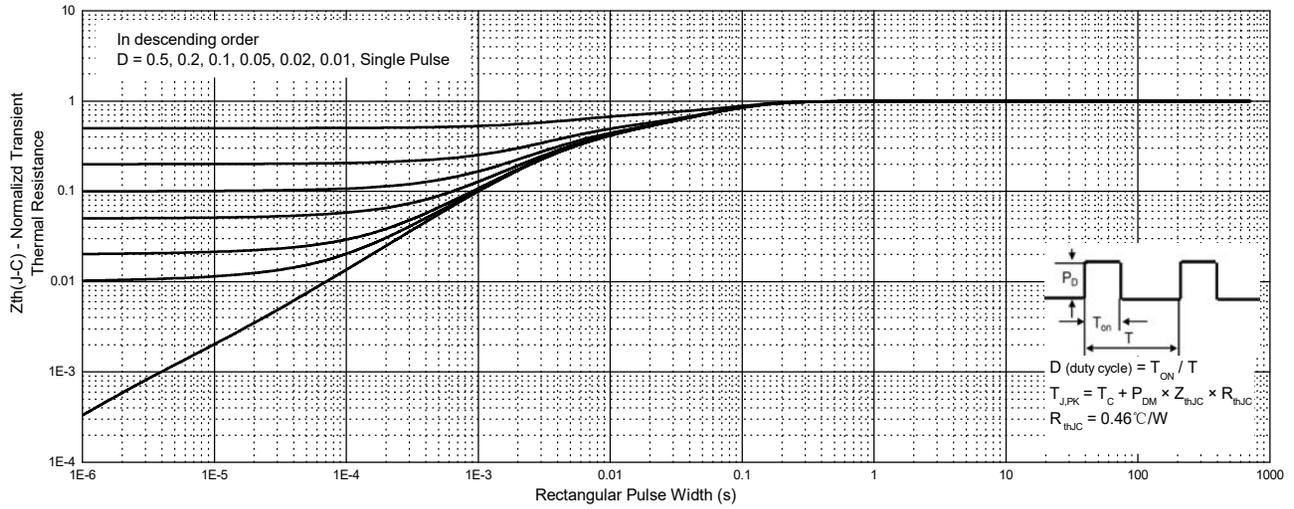


**Fig. 18 - Clamped Inductive Switching Energy vs. External Gate Resistor ( $R_{G(ext.)}$ )**



Curve Characteristics ( $T_J=25\text{ }^\circ\text{C}$  unless otherwise specified)

Fig.19 - Normalized Transient Thermal Impedance



## Ordering Information

Device	Packing
SICW040N120H4-BP	Tube:30pcs/Tube, 1.8K/Ctn;

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